

Atty. Dkt. No. 039153-0363 (F0804)

SUB  
B2A1  
Cont.

3 providing a first layer above a gate dielectric layer, the gate  
4 dielectric layer being above a substrate, the first layer including silicon oxynitride  
5 or silicon rich nitride;

6 providing a second layer above the first layer;

7 forming a first aperture in the second layer;

8 forming a second aperture in the first layer utilizing a RELACS  
9 process the second aperture being narrower than the first aperture;

10 filling the first aperture and the second aperture with a gate  
11 conductor material; and

12 removing the gate conductor material above the second layer.

1 16. (Amended) The method of claim 15, wherein

2 the second layer is an oxide layer [above the first layer and  
3 forming an aperture in the oxide layer before forming the aperture in the first  
4 layer].

SUB  
B4  
A2

1 19. (Amended) The method of claim 16, wherein the gate  
2 conductor material is silicided.